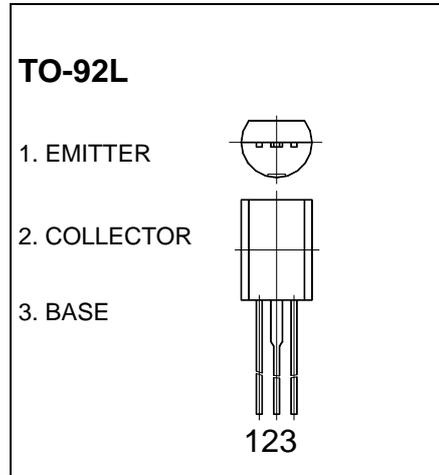




2SB892 TRANSISTOR (PNP)

FEATURE

- Power supplies, relay drivers, lamp drivers, and automotive wiring
- Low saturation voltage.
- Large current capacity and wide ASO.



MAXIMUM RATINGS (T_A=25°C unless otherwise noted)

Symbol	Parameter	Value	Units
V _{CB0}	Collector-Base Voltage	-60	V
V _{CE0}	Collector-Emitter Voltage	-50	V
V _{EBO}	Emitter-Base Voltage	-6	V
I _C	Collector Current -Continuous	-2	A
P _C	Collector Dissipation	0.75	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C

ELECTRICAL CHARACTERISTICS (T_{amb}=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	V(BR) _{CB0}	I _C = -100μA, I _E =0	-60		V
Collector-emitter breakdown voltage	V(BR) _{CE0}	I _C = -1mA, I _B =0	-50		V
Emitter-base breakdown voltage	V(BR) _{EBO}	I _E =- 100μA, I _C =0	-6		V
Collector cut-off current	I _{CB0}	V _{CB} = -50V, I _E =0		-0.1	μA
Emitter cut-off current	I _{EBO}	V _{EB} = -4V, I _C =0		-0.1	μA
DC current gain	h _{FE(1)}	V _{CE} =-2V, I _C = -100mA	100	560	
	h _{FE(2)}	V _{CE} =-2V, I _C = -1.5A	40		
Collector-emitter saturation voltage	V _{CE(sat)}	I _C = -1A, I _B = -50mA		-0.4	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C = -1A, I _B = -50mA		-1.2	V
Transition frequency	f _T	V _{CE} = -10 V, I _C = -50mA	150		MHz

CLASSIFICATION OF h_{FE(1)}

Rank	R	S	T	U
Range	100-200	140-280	200-400	280-560